Silicon NPN Power Transistors 2SD1884

DESCRIPTION

·With TO-3PML package
·High breakdown voltage
·High reliability.
·High speed

APPLICATIONS

·Color TV horizontal deflection output.
·Color display horizontal deflection output.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

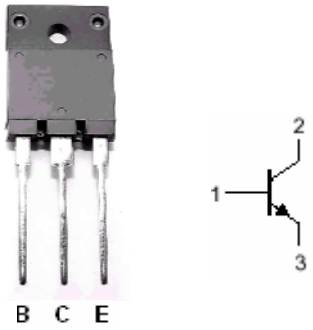


Fig.1 simplified outline (TO-3PML) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		5	A
I_{CM}	Collector current-peak		20	A
P_C	Collector power dissipation	T_C=25□	60	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	I_C=4A;I_B=0.8 A			5.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=4A;I_B=0.8 A			1.5	V
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=100mA;I_B=0	800			V
I_{EBO}	Emitter cut-off current	V_{EB}=4V; I_C=0			1	mA
I_{CBO}	Collector cut-off current	V_{CB}=800V; I_E=0			10	μA
I_{CES}	Collector cut-off current	V_{CE}=1500V; R_{BE}=0			1	mA
h_{FE-1}	DC current gain	I_C=1 A ; V_{CE}=5V	8			
h_{FE-2}	DC current gain	I_C=4A ; V_{CE}=5V	5		10	
t_f	Fall time	I_C=4A;R_L=50Ω; I_{B1}=0.8A I_{B2}=-1.6AV_{CC}=200V		0.1	0.3	μs

PACKAGE OUTLINE

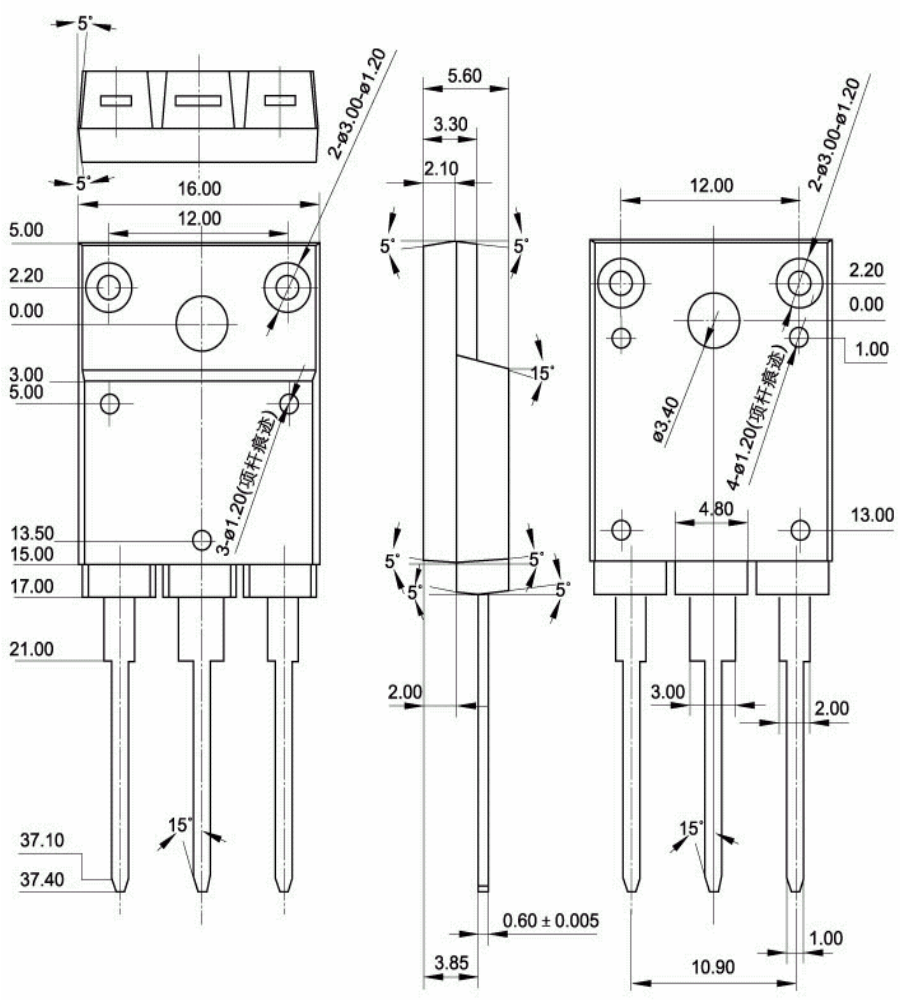


Fig.2 Outline dimensions

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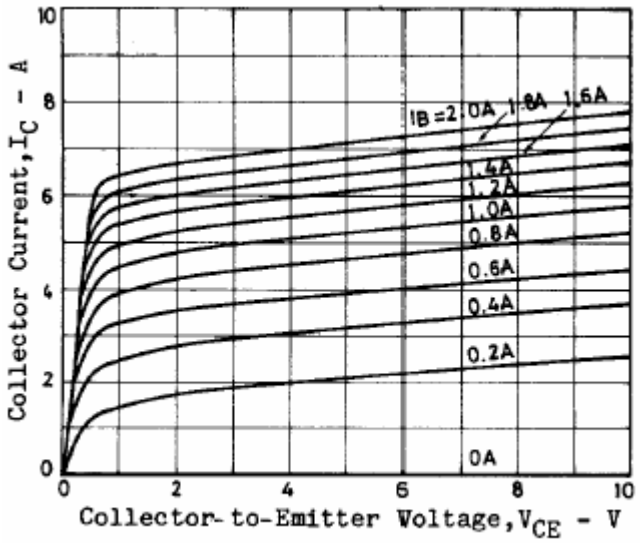


Fig.3 Static Characteristic

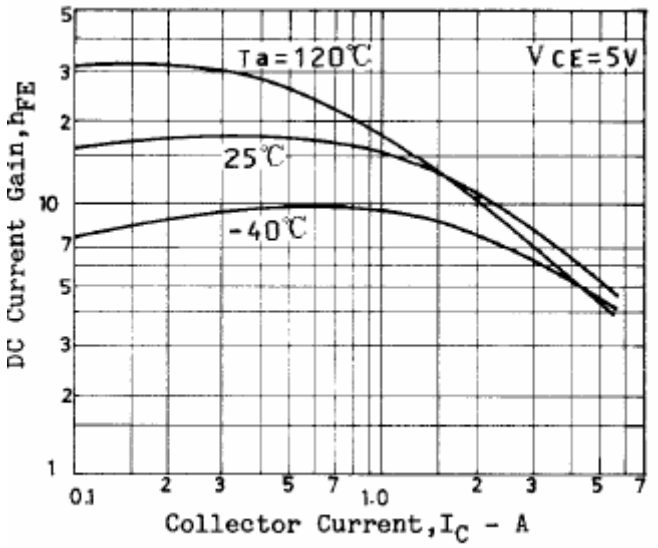


Fig.4 DC current Gain

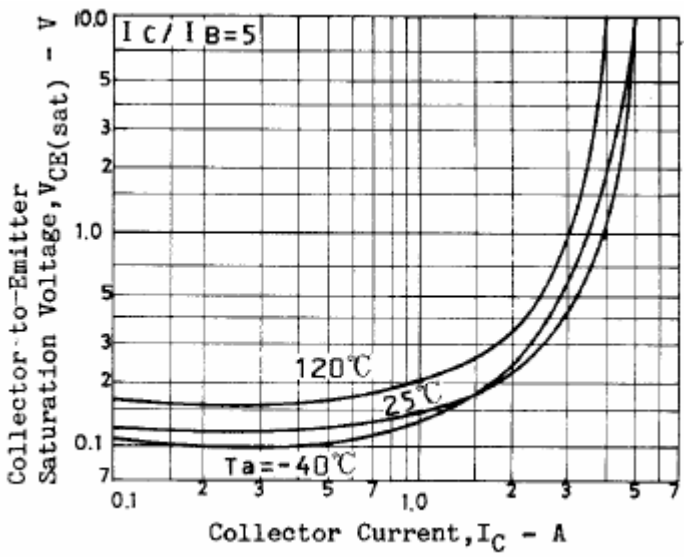


Fig.5 Collector-Emitter Saturation Voltage

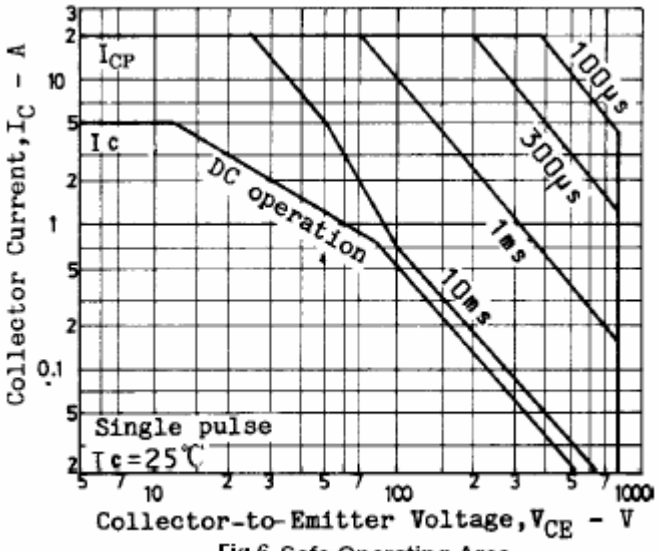


Fig.6 Safe Operating Area